

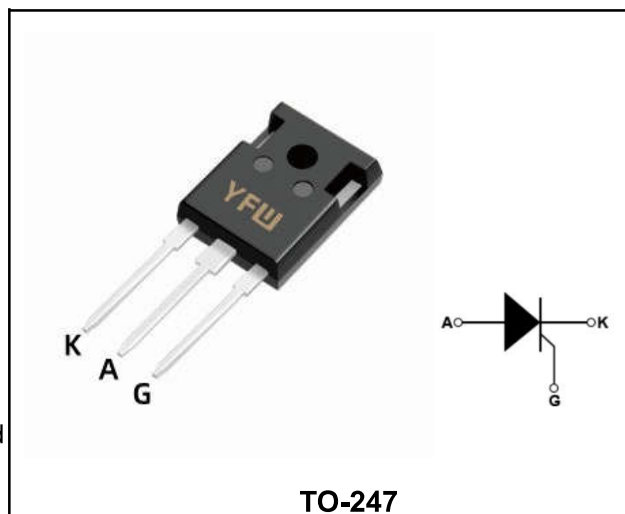
80A Silicon Control Rectifiers

Features

- ◆Single side grooving technology with independent intellectual property rights, table glass passivation technology;
- ◆Multi-layer metallized electrode;
- ◆High blocking voltage and high temperature Stability

Applications

Vacuum cleaners, power tools and other motor speed controllers; Solid state relays; Heating controllers (temperature regulation); And other phase control circuits.



Absolute maximum ratings ($T_{VJ}=25^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter and test conditions			value	Unit
$I_{T(AV)}$	On state average current $T_c=115^{\circ}\text{C}$ $T_{VJ}=150^{\circ}\text{C}$			80	A
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_c=115^{\circ}\text{C}$			126	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_{VJ} initial = 25°C)	$t=10\text{ms}$ $f=50\text{HZ}$	$T_{VJ}=45^{\circ}\text{C}$ $V_R=0$	900	A
I^2t	I^2t value for fusing	$t=10\text{ms}$ $f=50\text{HZ}$	$T_{VJ}=45^{\circ}\text{C}$ $V_R=0$	4050	A^2S
$(di/dt)_{cr}$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100 \text{ ns}$	$T_{VJ}=150^{\circ}\text{C}; f=50\text{Hz}$		150	A/us
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ}=25^{\circ}\text{C}$		1200	V
I_{GM}	Peak gate current	$t_p=20\mu\text{s}$ $T_{VJ}=125^{\circ}\text{C}$		8	A
V_{RGM}	Peak reverse gate voltage			5	V
$P_{G(AV)}$	Average gate power dissipation	$T_c=150^{\circ}\text{C}$		0.5	W
T_{stg} T_{VJ}	Storage junction temperature range Operating junction temperature range			$-40\text{to}+150$ $-40\text{to}+125$	$^{\circ}\text{C}$

Dynamic electrical characteristics ($T_{VJ}=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Parameter and test conditions			value	Unit
I _{GT}	V _D =6V	25℃ -40℃	MAX	60	mA
				122	
V _{GT}		25℃ -40℃	MAX	1.5	V
				1.6	
V _{GD}	V _D = ² / ₃ V _{DRM} T _{VJ} =150℃		MAX	0.2	V
I _{GD}				5	mA
I _H	V _D = 6V R _{GK} = ∞ T _{VJ} = 25℃		MAX	100	mA
I _L	t _p =10us I _G =0.3A; di _G /dt =0.3A/μs; T _{VJ} = 25℃		MAX	150	mA
t _{gd}	V _D =1/2 V _{DRM} T _{VJ} =25℃ I _G =0.3; di _G /dt=0.3A/us		MAX	2	us
t _q	V _R =100V; I _T =80A; V=2/3V _{DRM} T _{VJ} =125℃ di/dt=20A/us dv/dt=20V/us t _p =200us		Typ	150	us
(dv/dt) _{or}	V=2/3V _{DRM} R _{GK} = ∞ T _{VJ} =150℃		MAX	1000	V/us

Static electrical characteristics

Symbol	Parameter and test conditions			value	Unit
V_{TM}	$I_{TM}=160A$	$T_{VJ}=25^{\circ}\text{C}$	MAX	1.77	V
V_{T0}	Threshold on-state voltage	$T_{VJ}=150^{\circ}\text{C}$	MAX	0.88	V
R_d	Dynamic resistance	$T_{VJ}=125^{\circ}\text{C}$	MAX	6.4	$m\Omega$
$I_{R/D}$	$V_{R/D}=1200V$ $V_{R/D}=1200V$	$T_{VJ}=25^{\circ}\text{C}$ $T_{VJ}=125^{\circ}\text{C}$	MAX	50	μA
				5	mA
$R_{th(j-c)}$	Junction to ambient	BCB		0.6	$^{\circ}\text{C/W}$

Typical Characteristic Curves

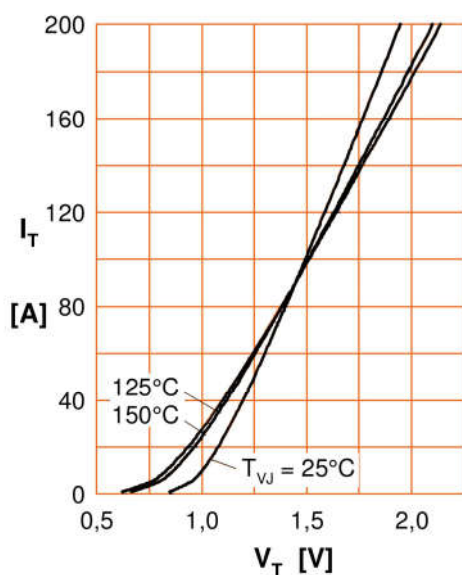


Fig. 1 Forward characteristics

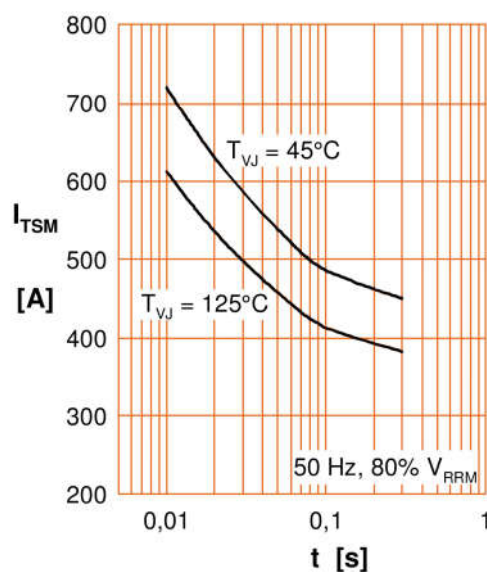


Fig. 2 Surge overload current

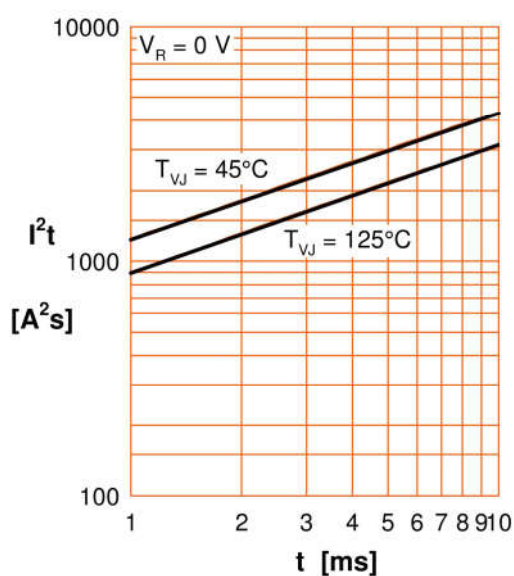


Fig. 3 I^2t versus time (1-10 ms)

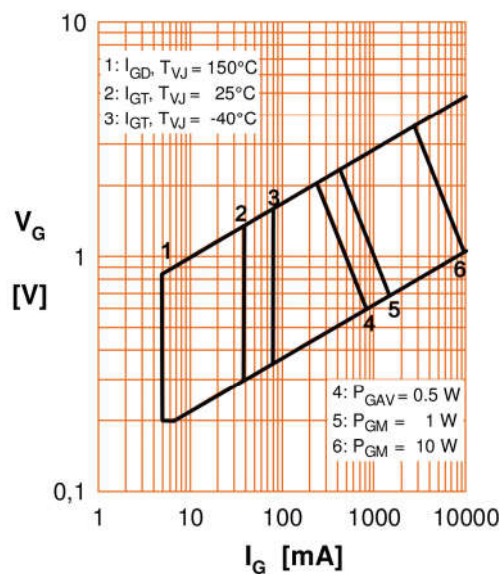


Fig. 4 Gate trigger characteristics

Typical Characteristic Curves

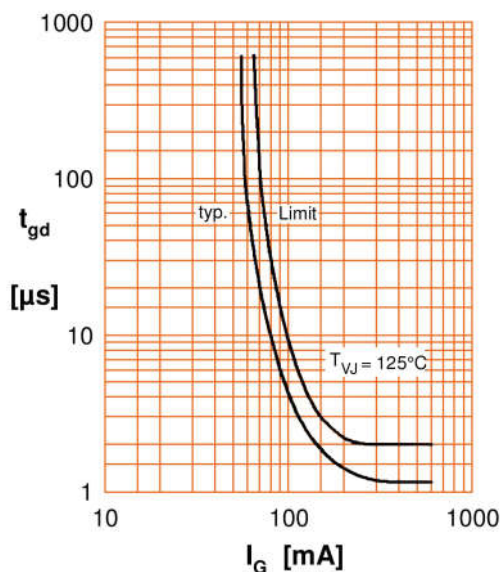


Fig. 5 Gate controlled delay time

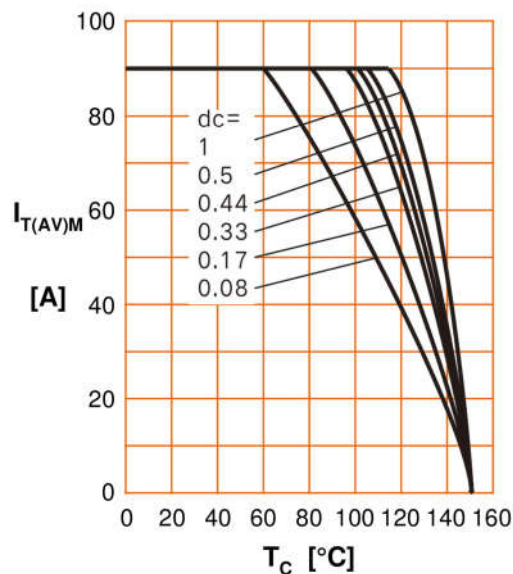


Fig. 6 Max. forward current at case temperature

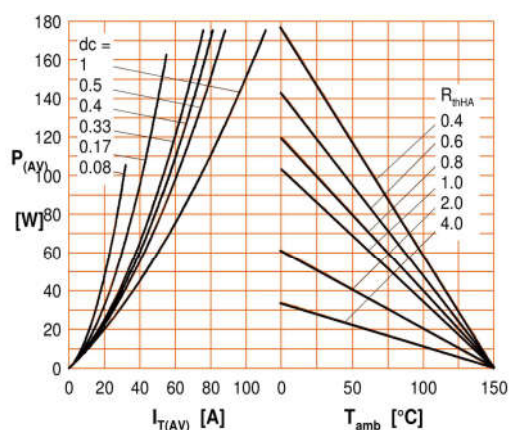


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

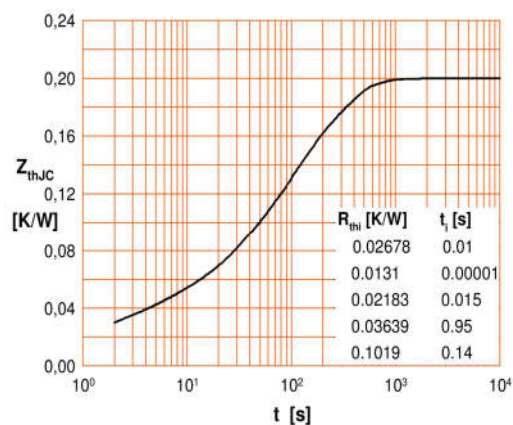
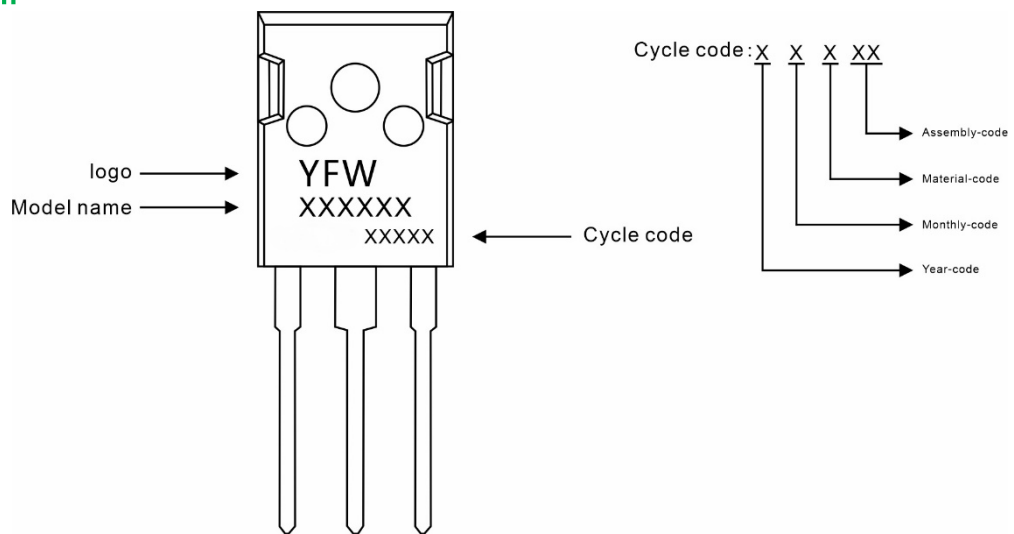


Fig. 8 Transient thermal impedance

Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
BCB80A	TO-247	0.209oz(5.93g)	30pcs/tube	600PCS/Box 2400PCS/Carton

Package Dimensions

TO-247

Symbol	Dimensions in mm		Dimensions in Inch	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	1.90	2.10	0.075	0.083
A2	2.29	2.54	0.090	0.100
b	1.00	1.40	0.039	0.055
b1	2.00	2.20	0.079	0.087
b2	3.00	3.20	0.118	0.126
c	0.50	0.70	0.020	0.028
D	15.75	16.05	0.620	0.632
E	20.20	20.80	0.795	0.819
e	5.45 (BSC)		0.215 (BSC)	
e1	10.90 (BSC)		0.429 (BSC)	
F	6.05	6.25	0.238	0.246
F1	5.80	6.00	0.228	0.236
L	20.10	20.40	0.791	0.803
L1	4.05	4.35	0.159	0.171
Φ	3.50	3.70	0.138	0.146

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